

## Supporting Information

# Rational Design of Interwoven SiO<sub>2</sub>@Gr/N-CNTs Heterostructures from Fe-C-Si Alloys for Achieving Superior Electromagnetic Wave Absorption

Jingyan Tang <sup>a</sup>, Qingguo Xue <sup>a</sup>, Jingsong Wang <sup>a, \*</sup>

<sup>a</sup> State Key Laboratory of Advanced Metallurgy, University of Science and Technology Beijing, Beijing 100083, China

\*Corresponding author.

Email address: wangjingsong@ustb.edu.cn (J.S. Wang)

### Electromagnetic absorbing performance calculation

The relative complex permittivity ( $\epsilon_r$ ) can be calculated as follows:

$$\epsilon_r = \epsilon_\infty + \frac{\epsilon_s - \epsilon_\infty}{1 + j2f\pi\tau} = \epsilon' - j\epsilon'' \quad (\text{S1})$$

Where  $\epsilon_r$  denotes the static permittivity,  $\epsilon_\infty$  represents the optical permittivity (relative dielectric permittivity in the high-frequency limit), and  $\tau$  corresponds to the relaxation time. The complex permittivity  $\epsilon_r$  comprises both real and imaginary components, where  $\epsilon'$  and  $\epsilon''$  signify the real part and imaginary part of permittivity, respectively. Through separation of the complex permittivity into its real and imaginary components, the following expressions can be derived:

$$\epsilon' = \epsilon_\infty + \frac{\epsilon_s - \epsilon_\infty}{1 + (2f\pi)^2\tau^2} \quad (\text{S2})$$

$$\epsilon'' = \epsilon_\infty + \frac{2\pi f\tau(\epsilon_s - \epsilon_\infty)}{1 + (2f\pi)^2\tau^2} \quad (\text{S3})$$

Based on Equations (S3) and (S4), the expression for  $\epsilon' - \epsilon''$  can be derived as:

$$(\epsilon' - \epsilon'')^2 + (\epsilon'')^2 = (\epsilon_r - \epsilon_\infty)^2 \quad (\text{S4})$$

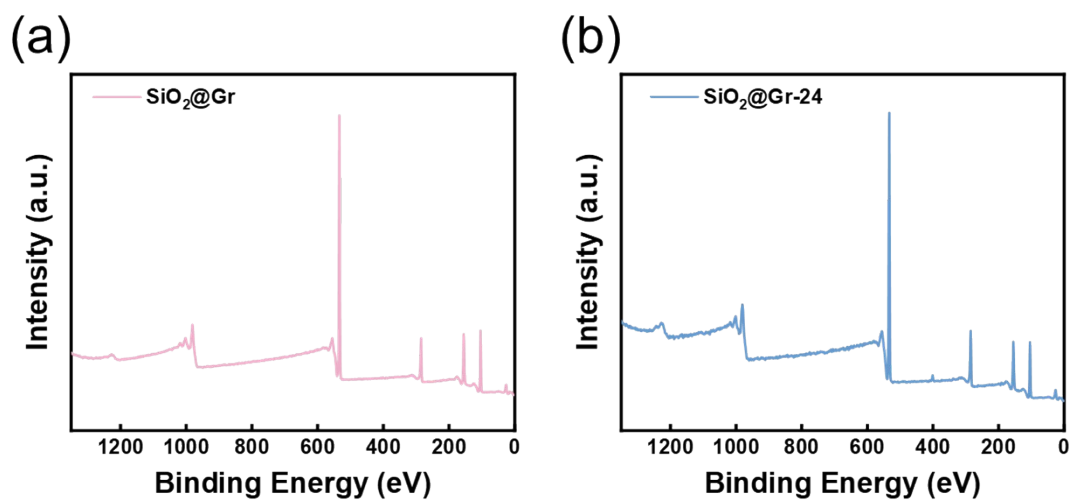
The attenuation constant ( $\alpha$ ) can be calculated using Equations (S5):

$$\alpha = \frac{\sqrt{2f\pi}}{c} \times \sqrt{(\epsilon''\mu'' - \epsilon'\mu')^2 + \sqrt{(\epsilon''\mu'' - \epsilon'\mu')^2 + (\epsilon'\mu'' + \epsilon'\mu')^2}} \quad (\text{S5})$$

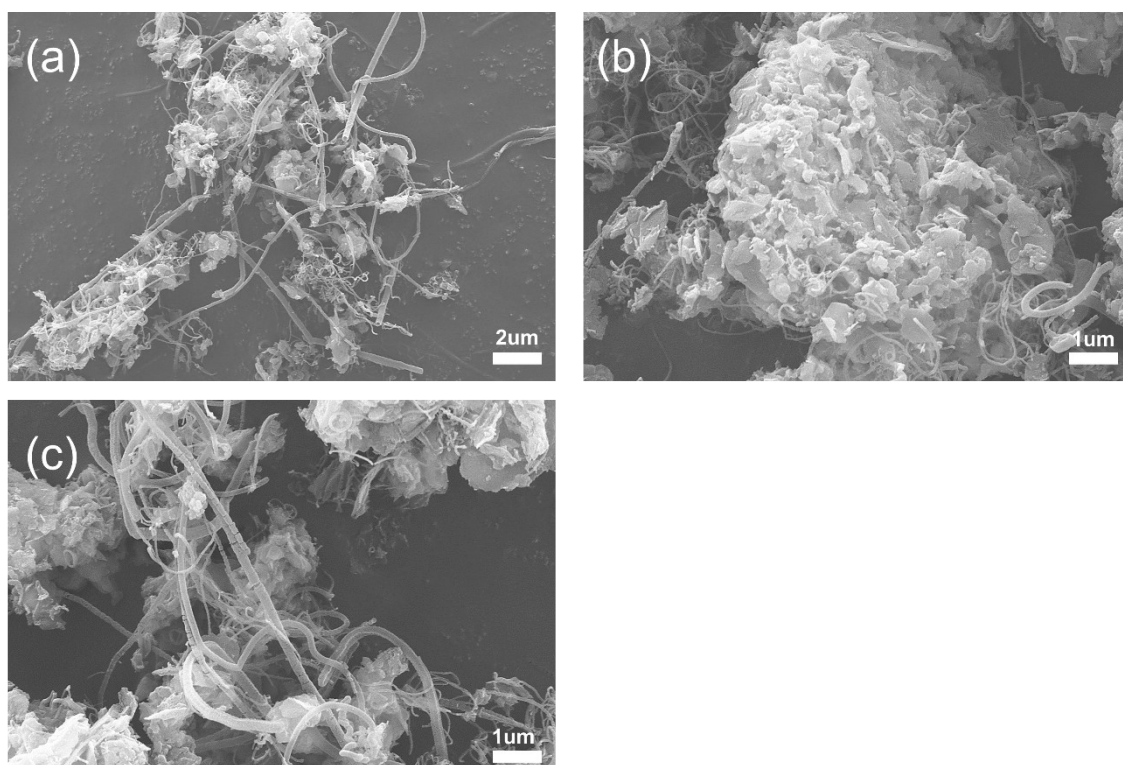
The impedance matching ( $Z_{in}/Z_0$ ) can be calculated using Equations (S6):

$$Z_{in} = |Z_{in}/Z_0| = \left| (\mu_r/\epsilon_r)^{1/2} \tanh \left[ j(2\pi f d/c)(\mu_r\epsilon_r)^{1/2} \right] \right| \quad (\text{S6})$$

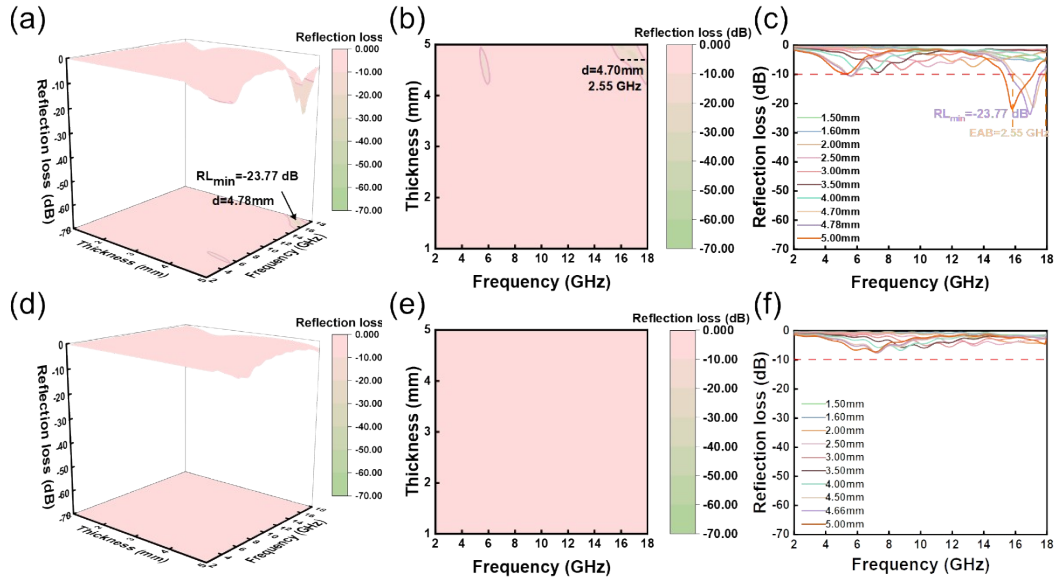




**Fig. S1** (a) The XPS full spectrum of  $\text{SiO}_2@\text{Gr}$ ; and (b) the XPS full spectrum of  $\text{SiO}_2@\text{Gr-24}$ .



**Fig.S2** (a)-(c) SEM images of  $\text{SiO}_2@\text{Gr}/\text{N-CNTs}$  at different multiples.



**Fig.S3** (a)-(c) The 3D and 2D diagrams and RL loss values of SiO<sub>2</sub>@Gr material. (d)-(f) The 3D and 2D diagrams and RL loss values of SiO<sub>2</sub>@Gr-24 material.

**Table S1** Analysis of Fe content in SiO<sub>2</sub>@Gr, SiO<sub>2</sub>@Gr-24, and SiO<sub>2</sub>@Gr/N-CNTs composite materials by ICP-OES

Samples	Fe (wt%)
SiO <sub>2</sub> @Gr	0.27
SiO <sub>2</sub> @Gr-24	0.31
SiO <sub>2</sub> @Gr/N-CNTs	0.91